



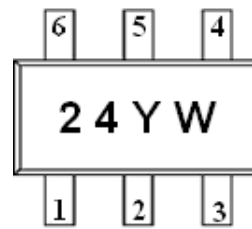
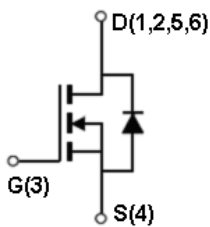
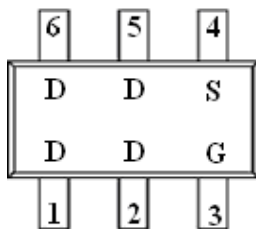
### General Description

AFN1424, N-Channel enhancement mode MOSFET, uses Advanced Trench Technology to provide excellent  $R_{DS(ON)}$ , low gate charge. These devices are particularly suited for low voltage power management, such as smart phone and notebook computer and other battery powered circuits, and low in-line power loss are needed in commercial industrial surface mount applications.

### Features

- 20V/5.0A,  $R_{DS(ON)}=30m\Omega@V_{GS}=4.5V$
- 20V/3.2A,  $R_{DS(ON)}=36m\Omega@V_{GS}=2.5V$
- 20V/2.4A,  $R_{DS(ON)}=46m\Omega@V_{GS}=1.8V$
- Super high density cell design for extremely low  $R_{DS(ON)}$
- Exceptional on-resistance and maximum DC current capability
- SOT-363 package design

### Pin Description ( SOT-363 )



### Application

- Portable Equipment
- Battery Powered System
- Net Working System

### Pin Define

Pin	Symbol	Description
1	D	Drain
2	D	Drain
3	G	Gate
4	S	Source
5	D	Drain
6	D	Drain

### Ordering Information

Part Ordering No.	Part Marking	Package	Unit	Quantity
AFN1424S36RG	24YW	SOT-363	Tape & Reel	3000 EA

- ※ 24 parts code
- ※ Y year code ( 0 ~ 9 )
- ※ W week code ( A ~ Z = 1 ~ 26 / a ~ z = 27 ~ 52 )
- ※ AFN1424S36RG : 7" Tape & Reel ; Pb- Free ; Halogen -Free



## Absolute Maximum Ratings

( $T_A=25^\circ\text{C}$  Unless otherwise noted)

Parameter	Symbol	Value	Unit	
Drain-Source Voltage	$V_{DSS}$	20	V	
Gate-Source Voltage	$V_{GSS}$	$\pm 12$	V	
Continuous Drain Current( $T_J=150^\circ\text{C}$ )	$I_D$	$T_A=25^\circ\text{C}$	4.0	A
		$T_A=70^\circ\text{C}$	3.2	
Pulsed Drain Current	$I_{DM}$	10	A	
Continuous Source Current(Diode Conduction)	$I_S$	0.9	A	
Power Dissipation	$P_D$	$T_A=25^\circ\text{C}$	1.0	W
		$T_A=70^\circ\text{C}$	0.52	
Operating Junction Temperature	$T_J$	150	$^\circ\text{C}$	
Storage Temperature Range	$T_{STG}$	-55/150	$^\circ\text{C}$	
Thermal Resistance-Junction to Ambient	$R_{\theta JA}$	120	$^\circ\text{C/W}$	

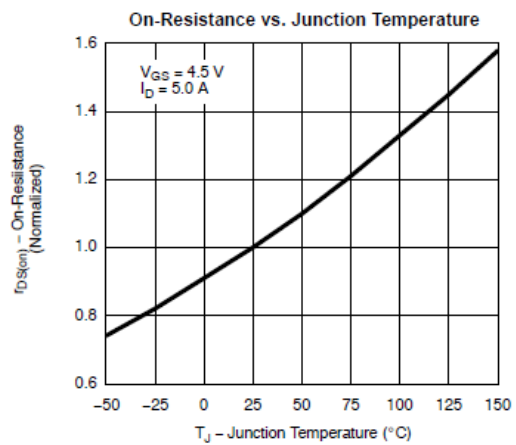
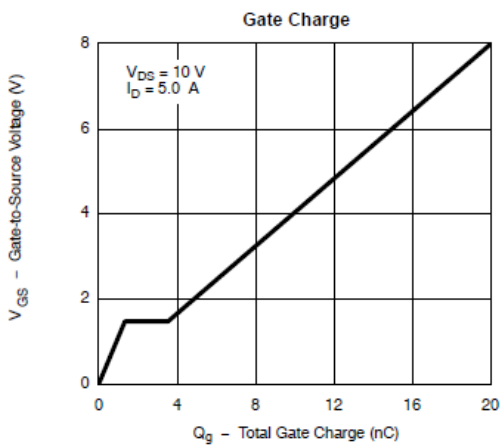
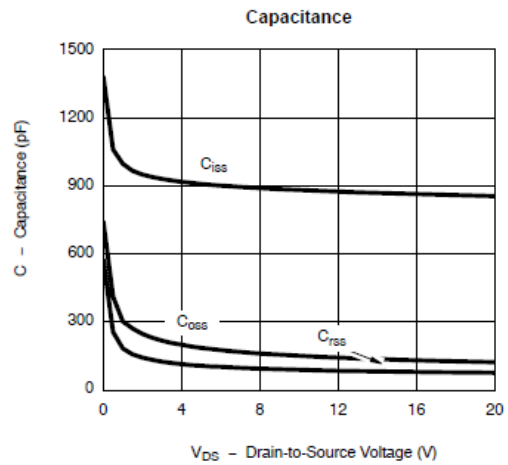
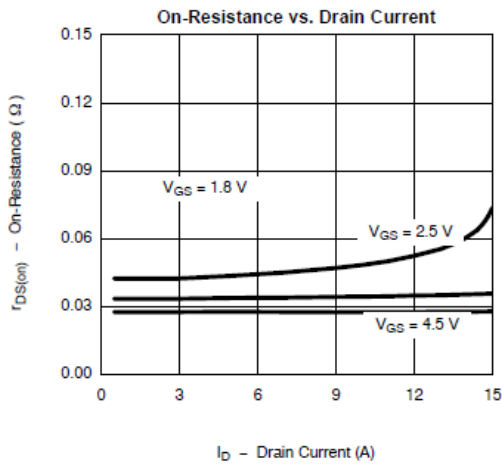
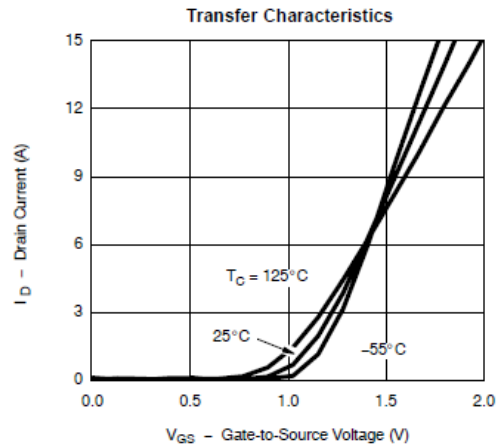
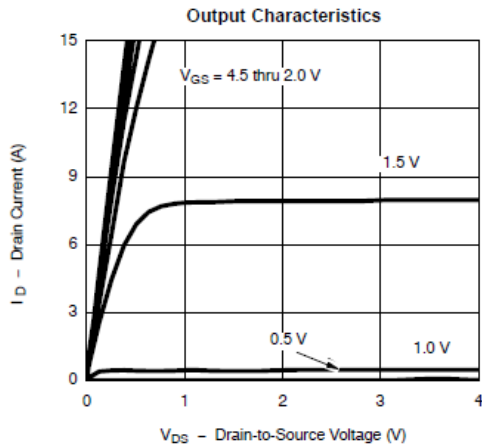
## Electrical Characteristics

( $T_A=25^\circ\text{C}$  Unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=250\mu\text{A}$	20			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu\text{A}$	0.45		0.85	
Gate Leakage Current	$I_{GSS}$	$V_{DS}=0V, V_{GS}=\pm 12V$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=16V, V_{GS}=0V$			1	$\mu\text{A}$
		$V_{DS}=16V, V_{GS}=0V$ $T_J=85^\circ\text{C}$			10	
On-State Drain Current	$I_{D(on)}$	$V_{DS} \geq 5V, V_{GS}=4.5V$	6			A
		$V_{DS} \geq 5V, V_{GS}=2.5V$	4			
Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=4.5V, I_D=5.0A$		25	30	m $\Omega$
		$V_{GS}=2.5V, I_D=3.2A$		29	36	
		$V_{GS}=1.8V, I_D=2.4A$		37	46	
Forward Transconductance	$g_{FS}$	$V_{DS}=5V, I_D=3.6A$		10		S
Diode Forward Voltage	$V_{SD}$	$I_S=1.6A, V_{GS}=0V$		0.85	1.2	V
<b>Dynamic</b>						
Total Gate Charge	$Q_g$	$V_{DS}=10V, V_{GS}=4.5V$ $I_D=4.0A$		11	15	nC
Gate-Source Charge	$Q_{gs}$			1.2		
Gate-Drain Charge	$Q_{gd}$			2.5		
Input Capacitance	$C_{iss}$	$V_{DS}=10V, V_{GS}=0V$ $f=1\text{MHz}$		600		pF
Output Capacitance	$C_{oss}$			205		
Reverse Transfer Capacitance	$C_{rss}$			60		
Turn-On Time	$t_{d(on)}$	$V_{DD}=10V, R_L=5.5\Omega$ $I_D=4.0A, V_{GEN}=4.5V$ $R_G=6\Omega$		15	25	ns
	$t_r$			40	60	
Turn-Off Time	$t_{d(off)}$			48	70	
	$t_f$			30	45	

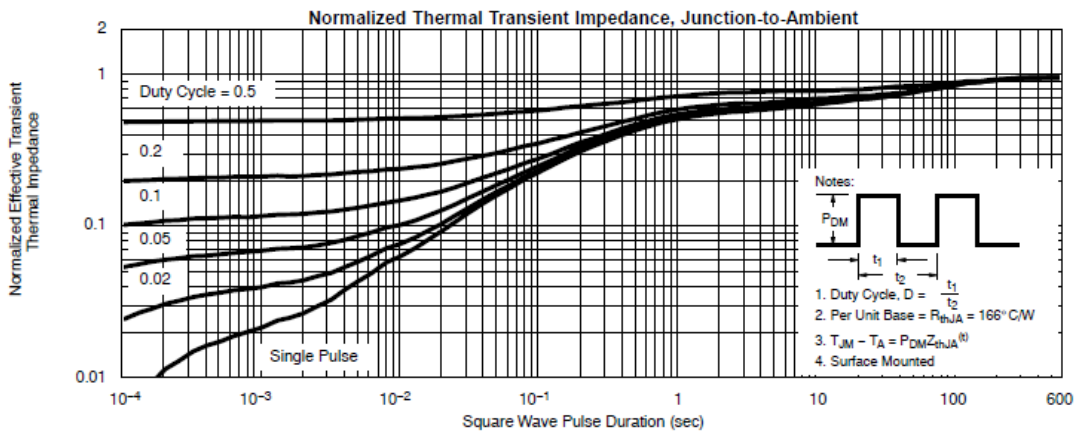
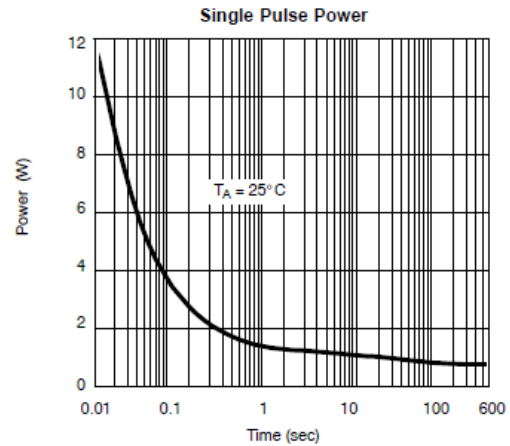
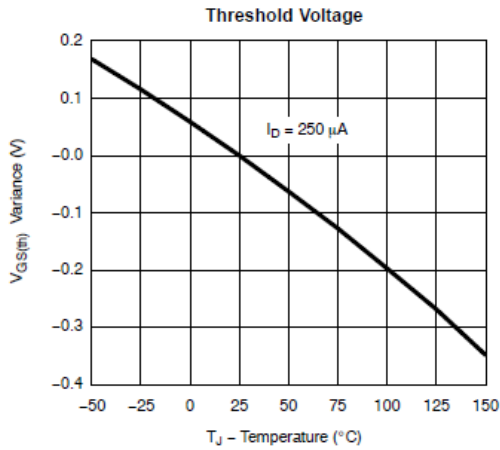
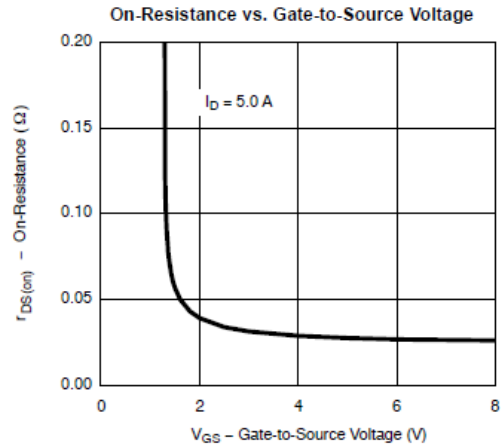
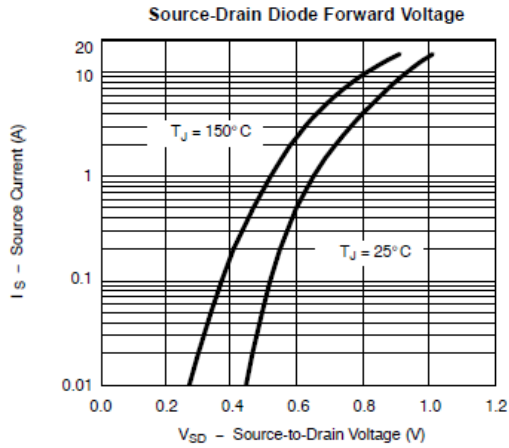


## Typical Characteristics





## Typical Characteristics





Typical Characteristics

Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms

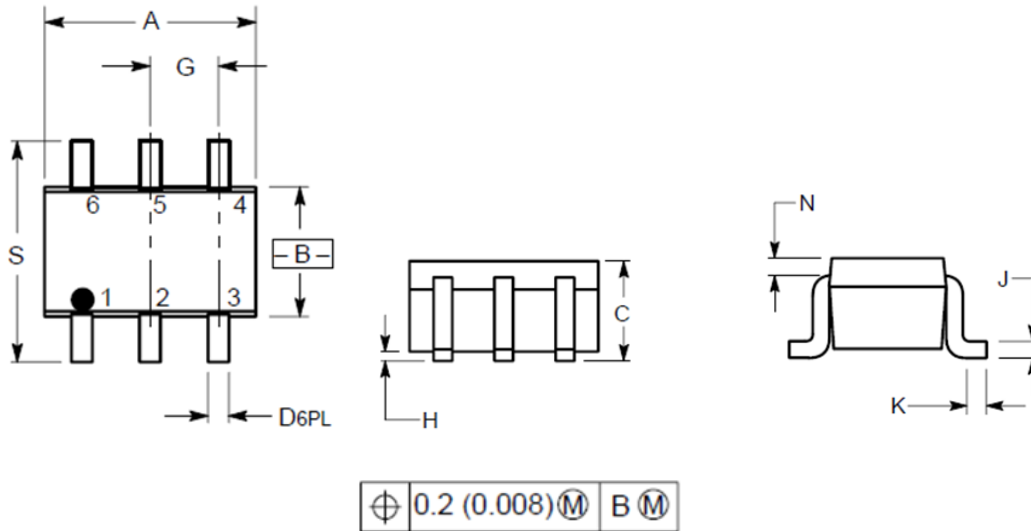


Unclamped Inductive Switching Test Circuit & Waveforms





**Package Information ( SOT-363 )**



DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.071	0.087	1.80	2.20
B	0.045	0.053	1.15	1.35
C	0.031	0.043	0.80	1.10
D	0.004	0.012	0.10	0.30
G	0.026 BSC		0.65 BSC	
H	---	0.004	---	0.10
J	0.004	0.010	0.10	0.25
K	0.004	0.012	0.10	0.30
N	0.008 REF		0.20 REF	
S	0.079	0.087	2.00	2.20

©2010 Alfa-MOS Technology Corp.  
 2F, No.80, Sec.1, Cheng Kung Rd., Nan Kang Dist., Taipei City 115, Taiwan (R.O.C.)  
 Tel : 886 2) 2651 3928  
 Fax : 886 2) 2786 8483  
 ©http://www.alfa-mos.com